NPN SILICON RF TRANSISTOR

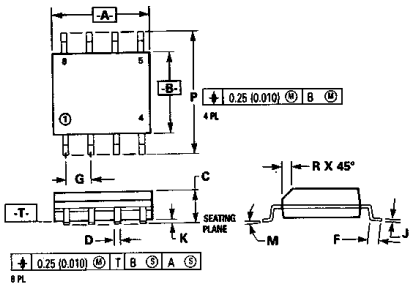
DESCRIPTION:

The **ASI MRF3866** is Designed for General Purpose Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	400 mA
V_{CE}	30 V
V_{CB}	55 V
V_{EB}	3.5 V
P_{DISS}	1.0 W @ T_C = 100 °C
T_J	-55 °C to +150 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	125 °C/W

PACKAGE STYLE



STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.80	5.00	0.189	0.196
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.18	0.25	0.007	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 5.0 mA			30			V
BV_{CBO}	I_C = 100 µA			55			V
BV_{EBO}	I_E = 100 µA			3.5			V
I_{CEO}	V_{CB} = 28 V					20	µA
h_{FE}	V_{CE} = 5.0 V	I_C = 360 mA		5.0			---
	V_{CE} = 5.0 V	I_C = 50 mA		10		200	
$V_{CE(sat)}$	I_C = 100 mA	I_B = 20 mA				250	mV
C_{OB}	V_{CB} = 30 V		f = 1.0 MHz			3.0	pF
f_t	V_{CE} = 15 V	I_C = 50 mA	f = 200 MHz		800		MHz

Specifications are subject to change without notice.